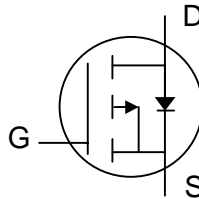




**P-channel Enhancement-mode Power MOSFET**

- Low Gate Charge
- Simple Drive Requirement
- Fast Switching Characteristic
- RoHS-compliant, halogen-free



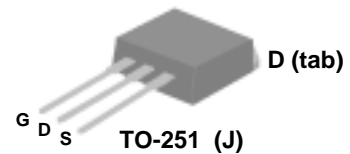
$BV_{DSS}$	-60V
$R_{DS(ON)}$	90mΩ
$I_D$	-15A

**Description**

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The AP9575GH-HF-3 is in the TO-252 package, which is widely used for commercial and industrial surface-mount applications, and is well suited for low voltage applications such as DC/DC converters.

The AP9575GJ-HF-3 is in the TO-251 through-hole package which is used where a small PCB footprint or an attached heatsink is required.



**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-60	V
$V_{GS}$	Gate-Source Voltage	±25	V
$I_D$ at $T_C=25^\circ C$	Continuous Drain Current	-15	A
$I_D$ at $T_C=100^\circ C$	Continuous Drain Current	-9.5	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	-45	A
$P_D$ at $T_C=25^\circ C$	Total Power Dissipation	31.3	W
	Linear Derating Factor	0.25	W/°C
$P_D$ at $T_A=25^\circ C$	Total Power Dissipation <sup>3</sup>	2	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

**Thermal Data**

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	4.0	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient (PCB mount) <sup>3</sup>	62.5	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient	110	°C/W

**Ordering Information**

**AP9575GH-HF-3TR** : in RoHS-compliant halogen-free TO-252, shipped on tape and reel (3000 pcs/reel)

**AP9575GJ-HF-3TB** : in RoHS-compliant halogen-free TO-251, shipped in tubes (80pcs/tube)



**Electrical Specifications at  $T_j=25^\circ\text{C}$  (unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-10V, I_D=-12A$	-	-	90	m $\Omega$
		$V_{GS}=-4.5V, I_D=-9A$	-	-	120	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-	-3	V
$g_{fs}$	Forward Transconductance	$V_{DS}=-10V, I_D=-9A$	-	14	-	S
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-60V, V_{GS}=0V$	-	-	-10	$\mu A$
	Drain-Source Leakage Current ( $T_j=125^\circ\text{C}$ )	$V_{DS}=-48V, V_{GS}=0V$	-	-	-250	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 25V, V_{DS}=0V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>2</sup>	$I_D=-9A$	-	14	27	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=-48V$	-	3	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=-4.5V$	-	8	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>2</sup>	$V_{DS}=-30V$	-	8	-	ns
$t_r$	Rise Time	$I_D=-9A$	-	17	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=-10V$	-	36	-	ns
$t_f$	Fall Time	$R_D=3.3\Omega$	-	41	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	1100	2660	pF
$C_{oss}$	Output Capacitance	$V_{DS}=-25V$	-	115	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	90	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$I_S=-9A, V_{GS}=0V$	-	-	-1.2	V
$t_{rr}$	Reverse Recovery Time <sup>2</sup>	$I_S=-9A, V_{GS}=0V,$	-	38	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di/dt=-100A/\mu s$	-	61	-	nC

**Notes:**

1. Pulse width limited by maximum junction temperature.
2. Pulse test - pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
3. Surface mounted on 1 in copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

APEC RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.



Typical Electrical Characteristics

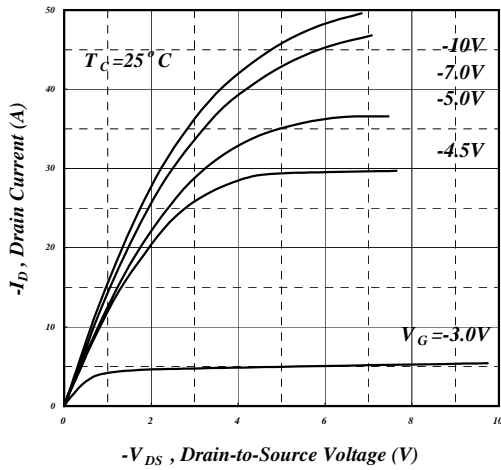


Fig 1. Typical Output Characteristics

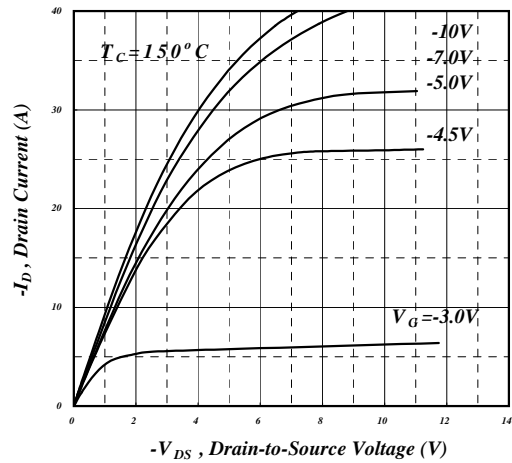


Fig 2. Typical Output Characteristics

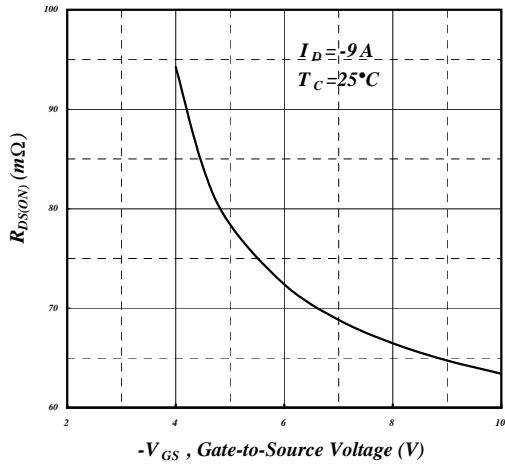


Fig 3. On-Resistance vs. Gate Voltage

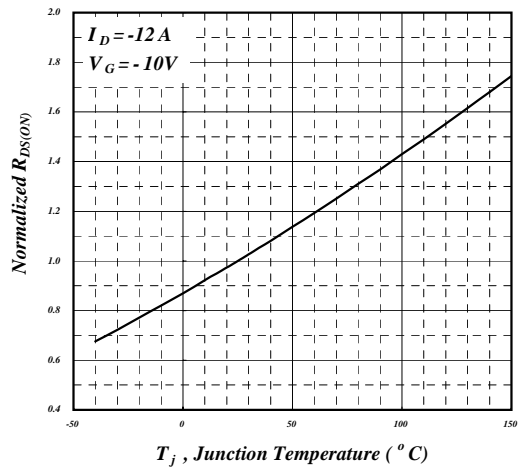


Fig 4. Normalized On-Resistance vs. Junction Temperature

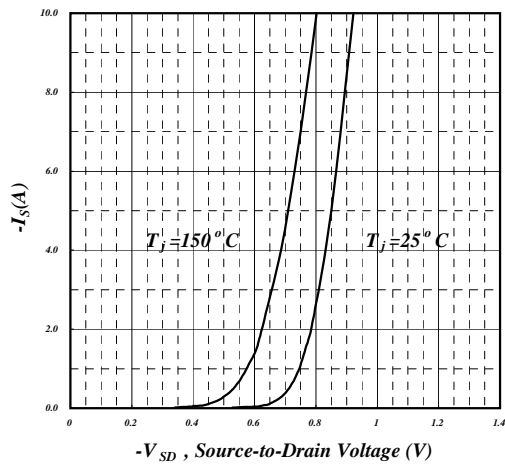


Fig 5. Forward Characteristic of Reverse Diode

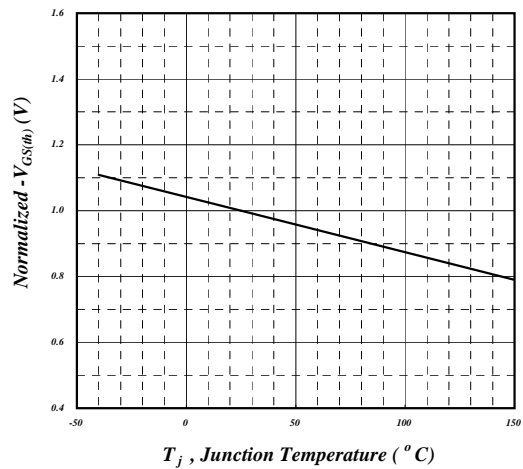


Fig 6. Gate Threshold Voltage vs. Junction Temperature



Typical Electrical Characteristics (cont.)

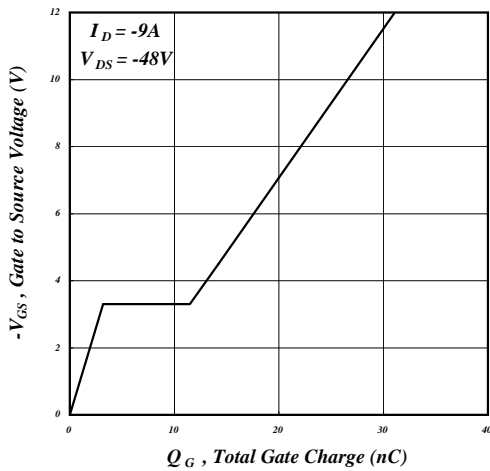


Fig 7. Gate Charge Characteristics

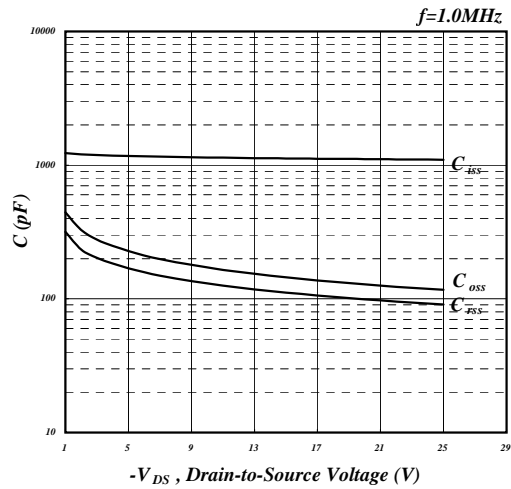


Fig 8. Typical Capacitance Characteristics

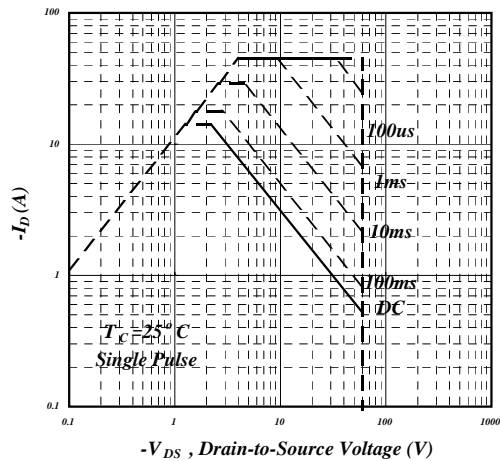


Fig 9. Maximum Safe Operating Area

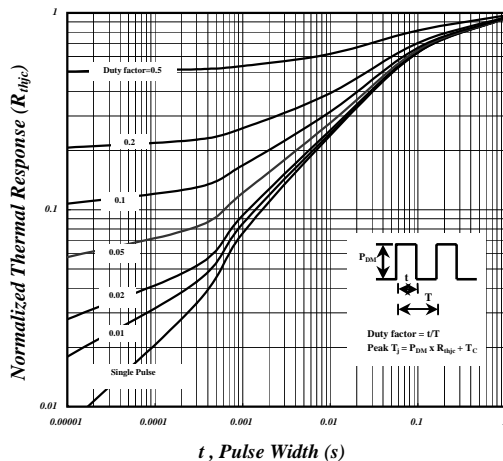


Fig 10. Effective Transient Thermal Impedance

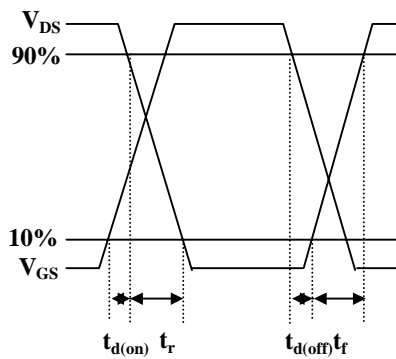


Fig 11. Switching Time Waveform

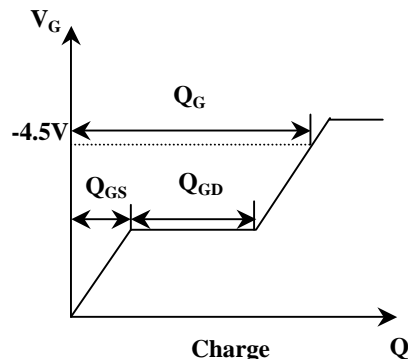


Fig 12. Gate Charge Waveform



**Package Dimensions: TO-252**



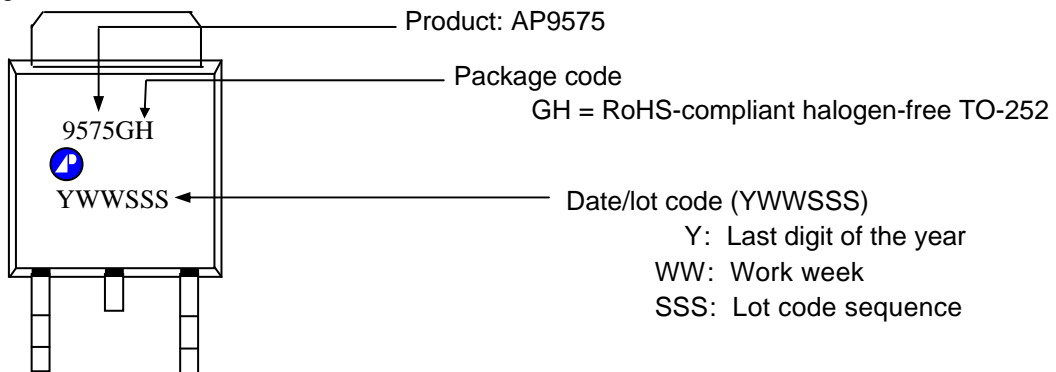
SYMBOLS	Millimeters		
	MIN	NOM	MAX
A2	1.80	2.30	2.80
A3	0.40	0.50	0.60
B1	0.40	0.70	1.00
D	6.00	6.50	7.00
D1	4.80	5.35	5.90
E3	3.50	4.00	4.50
F	2.20	2.63	3.05
F1	0.50	0.85	1.20
E1	5.10	5.70	6.30
E2	0.50	1.10	1.80
e	--	2.30	--
C	0.35	0.50	0.65

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.



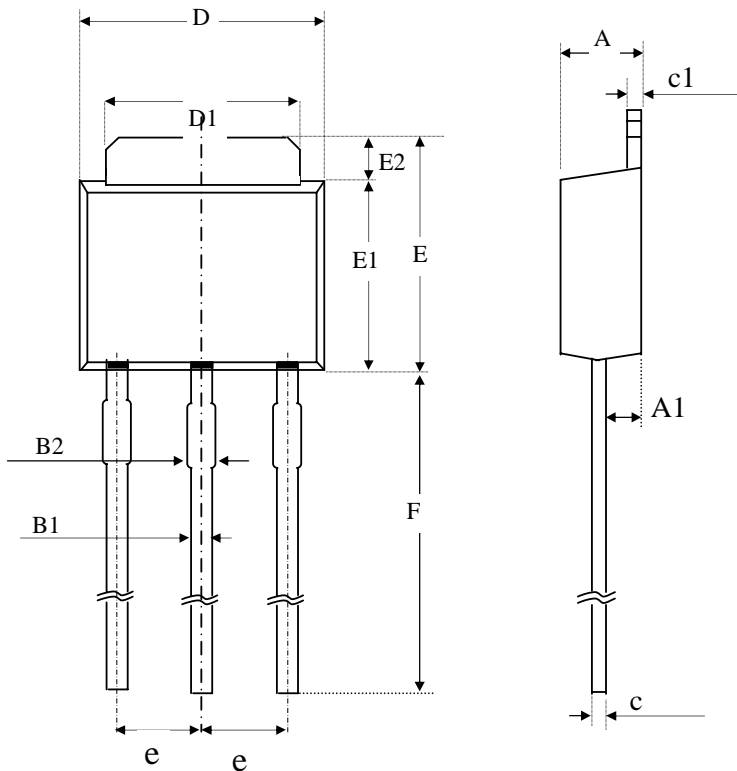
**Marking Information**

Laser Marking





**Package Dimensions: TO-251**



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.90	1.20	1.50
B1	0.40	0.60	0.80
B2	0.60	0.85	1.05
c	0.40	0.50	0.60
c1	0.40	0.50	0.60
D	6.40	6.60	6.80
D1	4.80	5.20	5.50
E	6.70	7.00	7.30
E1	5.40	5.60	5.80
E2	1.30	1.50	1.70
e	----	2.30	----
F	7.00	8.30	9.60

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.

**Marking Information**

